# 2SD0968A (2SD968A)

# Silicon NPN epitaxial planar type

For low-frequency driver amplification Complementary to 2SB0789A (2SB789A)

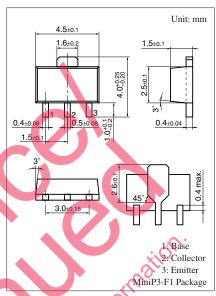
#### Features

- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Large collector power dissipation P<sub>C</sub>
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

# ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	120	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	120	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Peak collector current	$I_{CP}$	1	A	
Collector current	Ic	0.5	A	
Collector power dissipation *	P <sub>C</sub>	1	W	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to $+150$	°C	

Note) \*: Print circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion.



Marking Symbol: V

### ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{C} = 100  \mu A_{C} I_{B} = 0$	120			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_{\rm E} = 10  \mu A, I_{\rm C} = 0$	5			V
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	130		330	
	h <sub>EE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}$	50			
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.6	V
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.20	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$			20	pF
(Common base, input open circuited)						

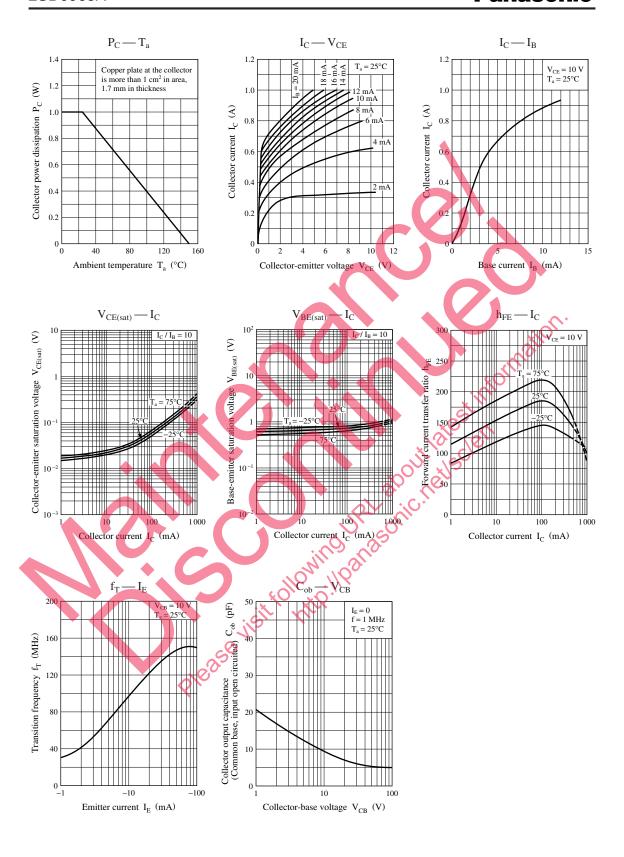
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*1: Pulse measurement

#### \*2: Rank classification

Rank	R	S
h <sub>FE1</sub>	130 to 220	185 to 330

Note) The part numbers in the parenthesis show conventional part number.



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